**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

### 2. Features and benefits

- High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- · Very sensitive gate

# 3. Applications

- General purpose low power motor control
- · General purpose switching and phase control

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions   | Min | Тур | Max  | Unit |
|---------------------|--|--|-----|-----|------|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |  | -   | -   | 600  | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{sp} \le 110 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3   | -   | -   | 1    | А    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; $Fig. 4$ ; $Fig. 5$                   | -   | -   | 12.5 | А    |
|                     |  | full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ;<br>$t_p = 16.7  \text{ms}$  | -   | -   | 13.8 | А    |
| Tj                  | junction temperature                     |  | -   | -   | 125  | °C   |
| Static chara        | acteristics                              |  |     |     |      |      |
| I <sub>GT</sub>     | gate trigger current                     | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 9</u>                  | -   | 0.4 | 3    | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $<br>$T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$ | -   | 1.3 | 3    | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$<br>$T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$            | -   | 1.4 | 3    | mA   |
|                     |  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 9</u>                  | -   | 3.8 | 7    | mA   |

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| Symbol                | Parameter                             | Conditions   |  | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|--|-----|-----|-----|------|
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>  |  | -   | 1.3 | 5   | mA   |
| V <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>   |  | -   | 1.2 | 1.5 | V    |
| Dynamic chara         | Dynamic characteristics               |  |  |     |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$ ; Fig. 14 |  | 10  | 20  | -   | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/dt$ = 0.5 A/ms; $I_T$ = 1 A; gate open circuit  |  | 2   | -   | -   | V/µs |

# 5. Pinning information

### **Table 2. Pinning information**

| Pin | Symbol | Description     | Simplified outline         | Graphic symbol |
|-----|--------|-----------------|----------------------------|----------------|
| 1   | T1     | main terminal 1 | 4                          | T2—T1          |
| 2   | T2     | main terminal 2 |                            | G<br>sym051    |
| 3   | G      | gate            |                            | symosi         |
| 4   | T2     | mainterminal 2  | ⊟1 ⊟2 ⊟3<br>SC-73 (SOT223) |                |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package |  |         |  |  |
|-------------|---------|--|---------|--|--|
|             | Name    | Description  | Version |  |  |
| BT131W-600  | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |  |  |

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                                | Conditions   | Min | Max  | Unit |
|---------------------|--|--|-----|------|------|
| $V_{DRM}$           | repetitive peak off-state voltage        |  | -   | 600  | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{sp} \le 110 ^{\circ}\text{C}$ ; $\overline{\text{Fig. 1}}$ ; $\overline{\text{Fig. 2}}$ ; $\overline{\text{Fig. 3}}$ | -   | 1    | Α    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5   | -   | 12.5 | Α    |
|                     |  | full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms   | -   | 13.8 | Α    |
| I <sup>2</sup> t    | I <sup>2</sup> t for fusing              | t <sub>p</sub> = 10 ms; SIN  | -   | 0.78 | A²s  |
| dl <sub>T</sub> /dt | rate of rise of on-state current         | I <sub>G</sub> = 6 mA  | -   | 50   | A/µs |
|                     |  |  | -   | 50   | A/µs |
|                     |  | I <sub>G</sub> = 14 mA   | -   | 10   | A/µs |
|                     |  | I <sub>G</sub> = 6 mA  | -   | 50   | A/µs |
| I <sub>GM</sub>     | peak gate current                        |  | -   | 2    | Α    |
| $P_{GM}$            | peak gate power                          |  | -   | 5    | W    |
| P <sub>G(AV)</sub>  | average gate power                       | over any 20 ms period  | -   | 0.5  | W    |
| T <sub>stg</sub>    | storage temperature                      |  | -40 | 150  | °C   |
| Tj                  | junction temperature                     |  | -   | 125  | °C   |

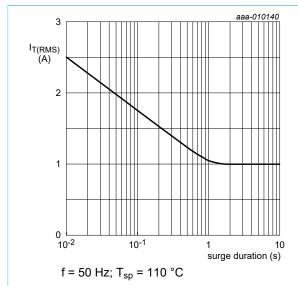


Fig. 1. RMS on-state current as a function of surge duration; maximum values

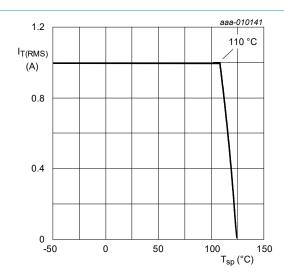


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

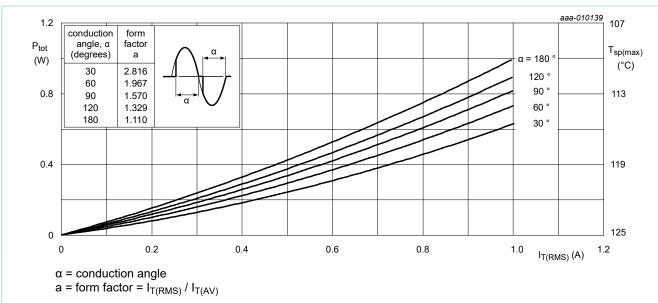


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

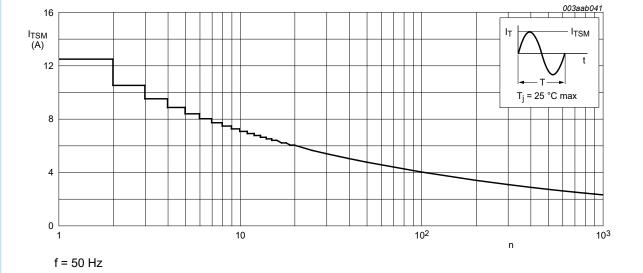
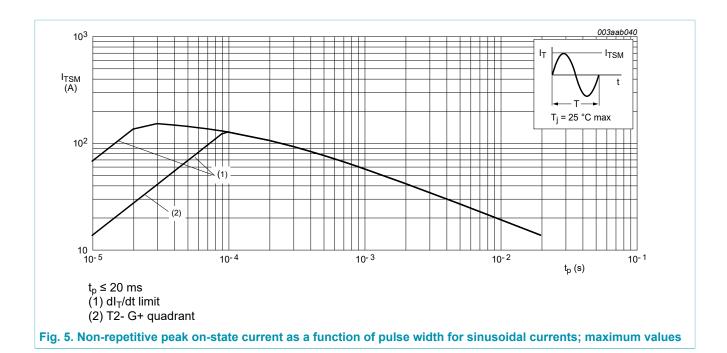


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

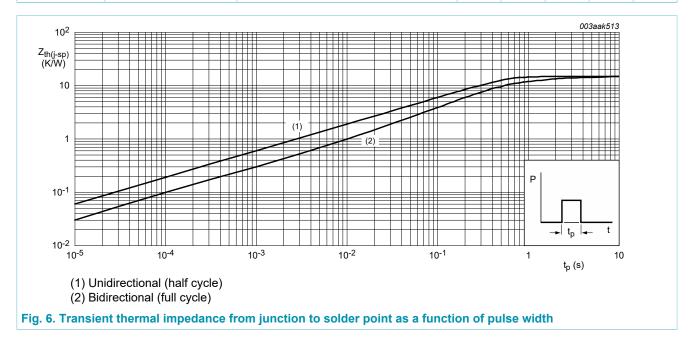


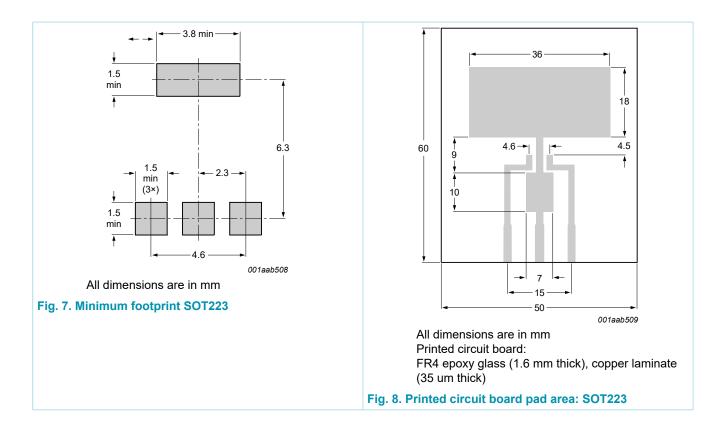
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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

| Symbol                | Parameter  | Conditions   | Min | Тур | Max | Unit |
|-----------------------|--|--|-----|-----|-----|------|
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point | full cycle; Fig. 6   | -   | -   | 15  | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance from junction to              | in free air; printed circuit board<br>mounted; minimum footprint; Fig. 7 | -   | 156 | -   | K/W  |
|                       | ambient free air                                 | in free air; printed circuit board<br>mounted; pad area; Fig. 8          | -   | 70  | -   | K/W  |





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### 9. Characteristics

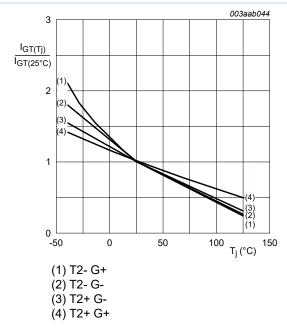
### **Table 6. Characteristics**

| Symbol                | Parameter                             | Conditions  | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|---|-----|-----|-----|------|
| Static chara          | acteristics                           |   | ,   |     |     |      |
| I <sub>GT</sub>       | gate trigger current                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 9$                                     | -   | 0.4 | 3   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{G-};$<br>$T_j = 25 \text{ °C}; Fig. 9$                              | -   | 1.3 | 3   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$             | -   | 1.4 | 3   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$             | -   | 3.8 | 7   | mA   |
| IL                    | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 10$                                    | -   | 1.2 | 5   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; Fig. 10$                                    | -   | 4   | 8   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. } 10}{\text{ C}}$  | -   | 1   | 5   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{T2- G+};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. } 10}{\text{C}}$    | -   | 2.5 | 8   | mA   |
| I <sub>H</sub>        | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>   | -   | 1.3 | 5   | mA   |
| $V_{T}$               | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>  | -   | 1.2 | 1.5 | V    |
| $V_{GT}$              | gate trigger voltage                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 13  | -   | 0.7 | 1   | V    |
|                       |                                       | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$<br>Fig. 13  | 0.2 | 0.3 | -   | V    |
| I <sub>D</sub>        | off-state current                     | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C   | -   | 0.1 | 0.5 | mA   |
| Dynamic ch            | aracteristics                         |   |     |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 kΩ; Fig. 14 | 10  | 20  | -   | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D$ = 400 V; $T_j$ = 125 °C; $dl_{com}/$<br>dt = 0.5 A/ms; $I_T$ = 1 A; gate open<br>circuit                          | 2   | -   | -   | V/µs |
| t <sub>gt</sub>       | gate-controlled turn-on time          | $I_{TM} = 1.5 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$                   | -   | 2   | -   | μs   |

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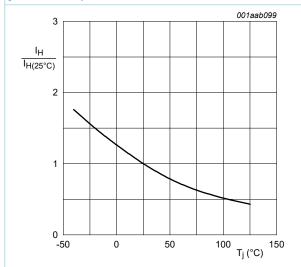
001aab100



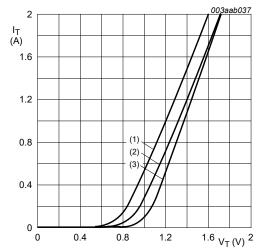
 $I_{\mathsf{L}}$ I<sub>L(25°C)</sub> 2 1 0 -50 0 50 100 <sub>Tj</sub> (°C) 150

Fig. 10. Normalized latching current as a function of junction temperature

Fig. 9. Normalized gate trigger current as a function of junction temperature



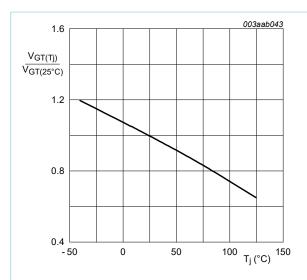




 $V_o$  = 0.92 V;  $R_s$  = 0.4 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage





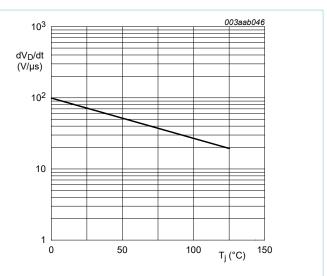


Fig. 14. Rate of rise of off-state voltage as a function of junction temperature; typical values

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# 10. Package outline

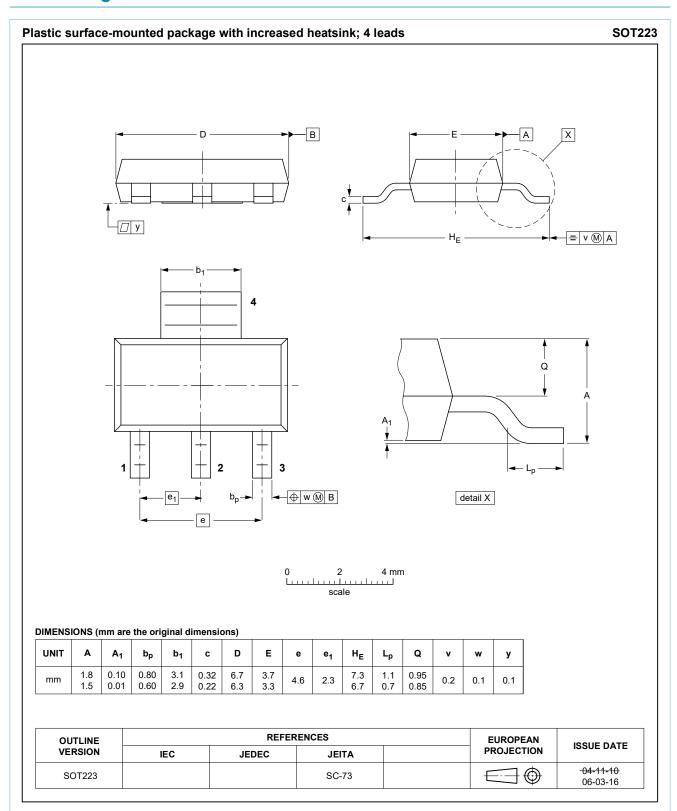
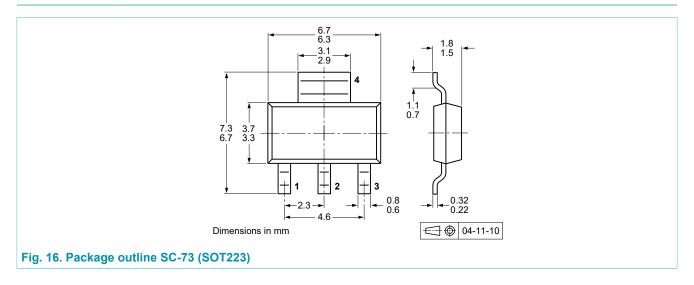


Fig. 15. Package outline SC-73 (SOT223)

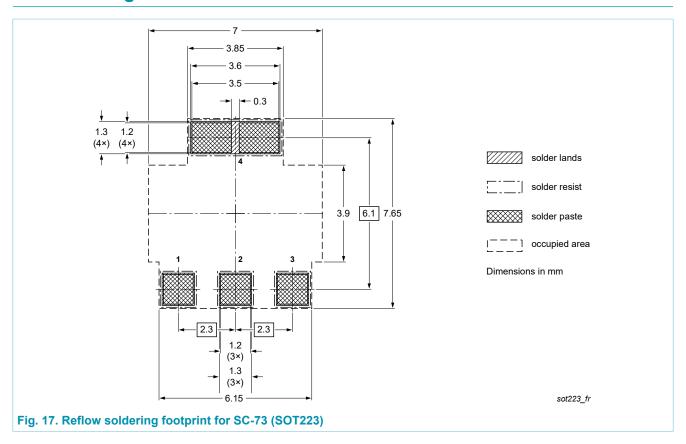
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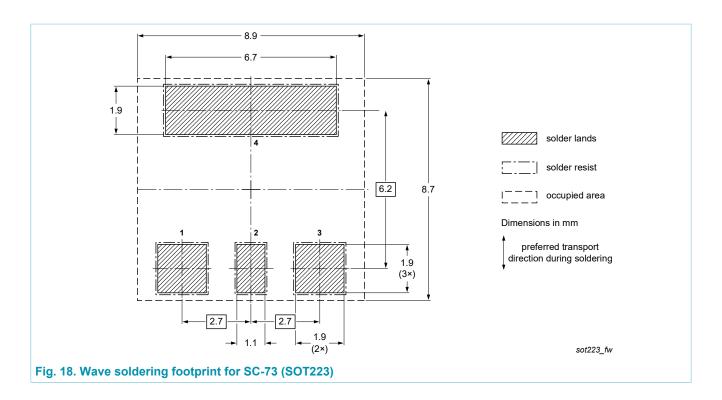
# 11. Package outline (minimized)



# 12. Soldering



**4Q Triac** 



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# 13. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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BT131W-600

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For more information, please visit: http://www.ween-semi.com
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Date of release: 15 June 2016

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